

Shuttling of Spin Polarized Electrons in Molecular Transistors

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(Dated: May 17, 2021)

Shuttling of electrons in single-molecule transistors with magnetic leads in the presence of an external magnetic field is considered theoretically. For a current of partially spin-polarized electrons a shuttle instability is predicted to occur for a finite interval of external magnetic field strengths. The lower critical magnetic field is determined by the degree of spin polarization and it vanishes as the spin polarization approaches 100%. The feasibility of detecting magnetic shuttling in a C_{60} -based molecular transistor with magnetic (Ni) electrodes is discussed [A. N. Pasupathy et al., *Science* **306**, 86 (2004)].

Keywords: single-electron shuttling, molecular transistors, spintronics

1. INTRODUCTION

In recent years the effect of the spin of electrons on the transport properties of nanostructures have been studied intensively, both theoretically and experimentally. In the context of spin-based electronics (spintronics) the possibility to control electrical currents by a weak external magnetic field using the Zeeman and/or the spin-orbit interaction is one of the main goals.

Magnetic materials and especially half-metals are natural sources of spin-polarized electrons for spintronics. Transport of spin-polarized electrons in nanostructures (quantum dots, suspended nanowires, etc.) in external magnetic field results in new phenomena where spin, charge and mechanical degrees of freedom are strongly inter-related. In this new field of investigations (spin-tromechanics, see Ref. 1) the presence of a mechanically “soft” subsystem results both in a strong enhancement of spintronic effects and in magnetic control of the mechanical subsystem in the classical as well as in the quantum transport regimes.

Vibrational effects are known to be important for the transport properties of molecular transistors (see, e.g., the reviews in Refs. 2 and 3). In single-molecule transistors a strong electron-vibron coupling was observed in a C_{60} -based transistor with nonmagnetic (gold) leads [4]. The measured current-voltage characteristics in this experiment revealed low-energy periodic step-like features. They were interpreted as a signature of vibron-assisted electron tunneling via the fullerene molecule. Experimental $I - V$ curves were theoretically explained [5, 6] in

the frames of a simple model of a single-level quantum dot strongly coupled to a single vibrational mode and weakly coupled to the source and drain electrodes.

Later on C_{60} -based molecular transistors with magnetic (Ni) leads were fabricated [7]. In samples where the tunneling coupling to the ferromagnetic electrodes were relatively strong (\sim tens of meV), Kondo-assisted tunneling via the C_{60} molecule was observed. These measurements also proved the presence of a strong inhomogeneous magnetic field produced by the ferromagnetic electrodes in the nano-gap between them. In samples with weak tunneling couplings the usual Coulomb blockade picture for a single-electron transistor was observed.

In the present paper we formulate the conditions for the appearance of a vibrational instability of a fullerene molecule suspended in the gap between two magnetic leads with opposite magnetization. Electron shuttling of spin-polarized electrons produced by magnetic (exchange) forces was predicted in Ref. 8 for the case of 100% polarization of the leads. In this limit (realized for half-metals) the electric current is blocked (spin blockade) in the absence of spin-flips induced by, e.g., an external magnetic field. It was shown that in the absence of dissipation in the mechanical subsystem such a magnetic field triggers a shuttle instability even for vanishingly small fields [8]. In the presence of dissipation a threshold magnetic field is determined by the rate of dissipation and it is small for a weak dissipation.

One of our aims here is to develop a theory of magnetic shuttling for conditions corresponding to the experimental set-up of Ref. 7, where the electrons in the ferromagnetic leads were partially polarized (\sim 30%). The absence of a spin blockade in this case qualitatively changes the criterion for electron shuttling. We will show that even in the absence of mechanical dissipation, a shuttling

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regime of electron transport occurs in a finite interval of external magnetic field strengths, $H_{\min} < H < H_{\max}$, where H_{\min} is determined by the degree of spin polarization η .

In particular, for a high degree of spin polarization ($\eta \rightarrow 1$) and if $\Gamma \gg \hbar\omega$ (where Γ/\hbar is the tunneling rate of majority spin electrons and $\omega/2\pi$ is the mechanical vibration frequency of the fullerene) the threshold magnetic field for reaching the shuttling regime of electron transport reads: $H_{\min} \sim \sqrt{\Gamma - \eta}\Gamma$. In the limit of ‘‘hard’’ vibrons, $\Gamma \ll \hbar\omega$, the threshold field is determined by the vibron energy, $H_{\min} \sim \sqrt{\Gamma - \eta}\hbar\omega$.

The calculations outlined below aim at determining the rate of change $r(H)$ (to be defined later) of the center-of-mass coordinate of the single-molecule shuttle, the sign of which then allows us to formulate the conditions required to observe shuttling of spin-polarized electrons in C_{60} -based molecular transistors.

2. HAMILTONIAN AND EQUATIONS OF MOTION

The Hamiltonian of a magnetically driven single electron shuttle (see Refs. 8 – 11) consists of four terms,

$$\hat{H} = \sum_{j=S,D} \left(\hat{H}_j + \hat{H}_{t,j} \right) + \hat{H}_d + \hat{H}_v, \quad (1)$$

where \hat{H}_j is the standard Hamiltonian of noninteracting electrons in the source ($j = S$) and drain ($j = D$) electrodes, $\hat{H}_{t,j}$ is a tunneling Hamiltonian with coordinate dependent tunneling amplitudes $t_j(\hat{x})$ and \hat{H}_d is the Hamiltonian of a single level (ε_0) quantum dot (QD) magnetically coupled to leads of spin-polarized electrons by coordinate dependent exchange interactions $J_j(\hat{x})$. It has been shown [3] that the shuttling regime of single-electron transport can be realized in the presence of an external magnetic field H_{ext} for oppositely magnetized source and drain electrodes. If the external magnetic field is directed perpendicular to the antiparallel polarization vectors of the leads, the QD Hamiltonian reads

$$\begin{aligned} \hat{H}_d = & \left[\varepsilon_0 - \frac{J(\hat{x})}{2} \right] a_{\uparrow}^{\dagger} a_{\uparrow} + \left[\varepsilon_0 + \frac{J(\hat{x})}{2} \right] a_{\downarrow}^{\dagger} a_{\downarrow} \\ & - \frac{g\mu H}{2} \left(a_{\uparrow}^{\dagger} a_{\downarrow} + a_{\downarrow}^{\dagger} a_{\uparrow} \right) + U a_{\uparrow}^{\dagger} a_{\uparrow} a_{\downarrow}^{\dagger} a_{\downarrow}. \end{aligned} \quad (2)$$

Here a_{σ}^{\dagger} (a_{σ}) is the creation (annihilation) operator for an electron with spin projection $\sigma = \uparrow, \downarrow$ on the dot, $J(\hat{x}) = J_S(\hat{x}) - J_D(\hat{x})$, μ is the Bohr magneton (g is the gyromagnetic ratio), and U is the Coulomb repulsion energy. QD vibrations are described by the harmonic oscillator Hamiltonian

$$\hat{H}_v = \frac{\hat{p}^2}{2m} + \frac{m\omega^2 \hat{x}^2}{2}, \quad (3)$$

where \hat{x} is the displacement operator, \hat{p} is the canonical conjugated momentum ($[\hat{x}, \hat{p}] = i\hbar$), m is the mass and ω is the (angular) vibration frequency of the QD.

The aim of the present paper is to find the conditions under which magnetically driven shuttling in experiments with fullerene-based single-molecule transistors [4, 7] can be realized. In this case the ferromagnetic leads are characterized by a certain degree $0 < \eta < 1$ of spin polarization ($\sim 30\%$ in the experiment of Ref. 7) and the characteristic vibron energy $\hbar\omega$ (\sim several meV, Ref. 4) is larger or of the order of the energy scale Γ that characterizes the tunneling coupling to the leads, $\Gamma \leq \hbar\omega$.

It follows from the above considerations that we are not in the adiabatic regime of mechanical motion (which is said to be antiadiabatic when $\Gamma \ll \hbar\omega$) and the physical picture of ‘‘magnetic shuttling’’ developed in Ref. 8 (see also Ref. 11) for the adiabatic regime does not hold here. As in Ref. 12 we will solve the problem using equations of motion for the reduced density operator. In the limit $eV \gg \Gamma$, $\hbar\omega$, μH , $k_B T$ (T is the temperature, V is the bias voltage) the density operator can be factorized into the product of a QD density operator and an equilibrium density matrix for the leads. In the Coulomb blockade regime, $eV, T \ll U$, the matrix elements of the QD density operator ($\rho_0 = \langle 0 | \hat{\rho}_d | 0 \rangle$, $\rho_{\sigma} = \langle \sigma | \hat{\rho}_d | \sigma \rangle$, $\rho_{\uparrow\downarrow} = \langle \uparrow | \hat{\rho}_d | \downarrow \rangle$) in the Hilbert space of a singly occupied dot level (they are still operators in the Hilbert space of a harmonic oscillator) are determined by the following set of equations [13],

$$\begin{aligned} \frac{\partial \rho_0}{\partial t} = & -i [H_v, \rho_0] - \frac{1}{2} \left\{ \Gamma_S^{\uparrow}(\hat{x}) + \Gamma_S^{\downarrow}(\hat{x}), \rho_0 \right\} \\ & + \sqrt{\Gamma_D^{\uparrow}(\hat{x})} \rho_{\uparrow} \sqrt{\Gamma_D^{\uparrow}(\hat{x})} + \sqrt{\Gamma_D^{\downarrow}(\hat{x})} \rho_{\downarrow} \sqrt{\Gamma_D^{\downarrow}(\hat{x})}, \end{aligned} \quad (4)$$

$$\begin{aligned} \frac{\partial \rho_{\uparrow}}{\partial t} = & -i [H_v, \rho_{\uparrow}] + \frac{i}{2} [J(\hat{x}), \rho_{\uparrow}] + \frac{i\hbar}{2} (\rho_{\uparrow\downarrow} - \rho_{\downarrow\uparrow}^{\dagger}) \\ & + \sqrt{\Gamma_S^{\uparrow}(\hat{x})} \rho_0 \sqrt{\Gamma_S^{\uparrow}(\hat{x})} - \frac{1}{2} \left\{ \Gamma_D^{\uparrow}(\hat{x}), \rho_{\uparrow} \right\}, \end{aligned} \quad (5)$$

$$\begin{aligned} \frac{\partial \rho_{\downarrow}}{\partial t} = & -i [H_v, \rho_{\downarrow}] - \frac{i}{2} [J(\hat{x}), \rho_{\downarrow}] - \frac{i\hbar}{2} (\rho_{\uparrow\downarrow} - \rho_{\downarrow\uparrow}^{\dagger}) \\ & + \sqrt{\Gamma_S^{\downarrow}(\hat{x})} \rho_0 \sqrt{\Gamma_S^{\downarrow}(\hat{x})} - \frac{1}{2} \left\{ \Gamma_D^{\downarrow}(\hat{x}), \rho_{\downarrow} \right\}, \end{aligned} \quad (6)$$

$$\begin{aligned} \frac{\partial \rho_{\uparrow\downarrow}}{\partial t} = & -i [H_v, \rho_{\uparrow\downarrow}] + \frac{i}{2} \{ J(\hat{x}), \rho_{\uparrow\downarrow} \} + \frac{i\hbar}{2} (\rho_{\uparrow} - \rho_{\downarrow}) \\ & - \frac{\rho_{\uparrow\downarrow}}{2} \Gamma_D^{\downarrow}(\hat{x}) - \Gamma_D^{\uparrow}(\hat{x}) \frac{\rho_{\uparrow\downarrow}}{2}. \end{aligned} \quad (7)$$

In order to solve Eqs. (4) – (7) it is convenient to introduce dimensionless variables for time ($t\omega \rightarrow t$), dot displacement ($\hat{x}/x_0 \rightarrow \hat{x}$, where $x_0 = \sqrt{\hbar/m\omega}$ is the zero-point oscillation amplitude), momentum ($\hat{p}x_0/\hbar \rightarrow \hat{p}$) and for various characteristic energies ($\hbar\omega \rightarrow 1$, $g\mu H/\hbar\omega \rightarrow h$, $\Gamma_j^{\sigma}(\hat{x})/\hbar\omega \rightarrow \Gamma_j^{\sigma}(\hat{x})$, where $\Gamma_j^{\sigma}(\hat{x}) = 2\pi\nu |t_{j,\sigma}(\hat{x})|^2$ is the level width, ν is the density of states).

3. INFLUENCE OF SPIN POLARIZATION ON THE MAGNETIC SHUTTLE INSTABILITY

We are interested in the conditions under which a magnetic shuttle instability occurs. Therefore it is sufficient to expand tunneling amplitudes and exchange energies up to linear terms in the coordinate operator \hat{x} ,

$$J(\hat{x}) = J_0 - \alpha\hat{x}, \quad \Gamma_{S/D}^\sigma(\hat{x}) = \Gamma_{S/D}^\sigma \left(1 \mp \frac{\hat{x}}{l} \right), \quad (8)$$

where l is the characteristic electron tunneling length (of the order of 1 Å).

Note that the zero-point fluctuation amplitude of a fullerene molecule in the vicinity of the Lennard-Jones potential minimum is much smaller than the electron tunneling length, $l \gg 1$. Since the spatial scale of the exchange interaction is also determined by the tunneling length l , we can treat the mechanical coordinate \hat{x} as a classical variable. The equation of motion for the classical coordinate x_c takes the form

$$\frac{d^2 x_c}{dt^2} + x_c = -\frac{\alpha}{2} \text{Tr}(\rho_\uparrow - \rho_\downarrow). \quad (9)$$

The r.h.s. of Eq. (9) can readily be found from the set of linear equations (4) – (7) when the operator \hat{x} is replaced by x_c .

To simplify analytical calculations we consider a symmetric junction for which $J_0 = 0$, $\Gamma_S^\uparrow = \Gamma_D^\downarrow = \Gamma$, and $\Gamma_S^\downarrow = \Gamma_D^\uparrow = \gamma$. To first order in the small dimensionless parameter $\alpha/l \sim (J/\hbar\omega)(x_0/l)^2 \ll 1$ Eq. (9) is reduced to a linear equation. For the time dependent coordinate displacement $x_1 = x_1(t)$ this equation reads

$$\frac{d^2 x_1}{dt^2} + x_1 = -\frac{\alpha}{2l} \int_{-\infty}^t dt' \langle e_0 | e^{\hat{A}(t-t')} | e \rangle x_1(t'). \quad (10)$$

Here the matrix \hat{A} takes the form

$$\hat{A} = \frac{1}{2} \begin{pmatrix} -\Gamma_1 & -\Gamma_2 & -2h \\ \Gamma_2 & -3\Gamma_1 & 0 \\ 2h & 0 & -\Gamma_1 \end{pmatrix}, \quad (11)$$

$\Gamma_{1,2} = \Gamma \pm \gamma$, $|e_0\rangle = (1, 0, 0)^T$, and the vector $|e\rangle = (e_1, e_2, e_3)^T$ has the components

$$\begin{aligned} e_1 &= -\frac{2\Gamma_2}{\Delta}(\Gamma_1^2 - \Gamma_2^2), \quad e_2 = -\frac{2\Gamma_1}{\Delta}(\Gamma_1^2 - \Gamma_2^2 + 4h^2) \\ e_3 &= -\frac{4h\Gamma_1\Gamma_2}{\Delta}, \quad \Delta = 3\Gamma_1^2 + \Gamma_2^2 + 12h^2. \end{aligned} \quad (12)$$

A shuttle instability occurs when the oscillatory solution of Eq. (10), $x_1(t) \sim \exp(i\Omega t)$ becomes unstable, that is when $\text{Im}\Omega < 0$. The smallness of the r.h.s. of Eq. (10) allows one to obtain the imaginary part of Ω by perturbation theory. The values of the parameters Γ_1, Γ_2 and h

for which $\text{Im}\Omega < 0$, corresponding to the shuttle regime of electron transport, satisfy the inequality

$$h^4 + A_1 h^2 + A_2 < 0, \quad (13)$$

where

$$A_1 = -3(\Gamma_1^2 + 1) - \frac{\Gamma_1^2 - \Gamma_2^2}{8\Gamma_1^2} (5\Gamma_1^2 + 4), \quad (14)$$

$$A_2 = \frac{(\Gamma_1^2 - \Gamma_2^2)(\Gamma_1^2 + 4)}{8\Gamma_1^2} \left(\Gamma_1^2 + 1 + \frac{\Gamma_1^2 - \Gamma_2^2}{4} \right). \quad (15)$$

Note that in the absence of an external magnetic field the nanoelectromechanical coupling results in additional damping of the mechanical subsystem (since the coefficient $A_2 > 0$).

It is evident from Eq. (13), which is biquadratic in the magnetic field (h), that a shuttle instability occurs in a finite interval of magnetic fields, $h_{\min} < h < h_{\max}$. Now we introduce the degree of spin polarization as

$$\eta = \frac{|N_\uparrow - N_\downarrow|}{N_\uparrow + N_\downarrow} \simeq \frac{\Gamma - \gamma}{\Gamma + \gamma} \quad (16)$$

where N_σ is the number of particles with spin projection σ . The last relation in Eq. (16) comes from the definition of tunneling rates and our assumption that tunneling amplitudes do not depend on spin projections. We analyze Eq. (13) in two limiting cases: (i) $\Gamma \gg 1$, $1 - \eta \ll 1$, and (ii) $\Gamma \ll 1$, $1 - \eta \ll 1$.

Note that in the limit of weak polarization, $\eta \rightarrow 0$, magnetic forces are small, $J \rightarrow 0$, and electron shuttling is supported by Coulomb forces. This case was considered in Ref. 12, where it was shown that in the limit of weak polarization a magnetic field ceases to influence single electron shuttling.

In the adiabatic limit, (i), one finds (reverting to using parameters with dimensions) that the shuttle instability region is defined by the double inequality

$$\frac{\Gamma}{2} \sqrt{\frac{1-\eta}{3}} < g\mu H < \sqrt{3}\Gamma. \quad (17)$$

In the antiadiabatic limit, (ii), the critical magnetic fields are determined by the vibron energy $\hbar\omega$ rather than the tunneling rate Γ , so that

$$\hbar\omega \sqrt{\frac{1-\eta}{3}} < g\mu H < \sqrt{3}\hbar\omega. \quad (18)$$

For the general case that part of the Γ, H parameter space which corresponds to a magnetic shuttle instability is shown in Fig. 1 for different degrees of spin polarization. For a given (normalized) tunneling coupling $\Gamma/\hbar\omega$ the range of magnetic fields for which an instability occurs is shifted towards higher fields as the spin polarization decreases. The upper critical field for high spin polarizations, $\eta \rightarrow 1$, depends linearly on η ,

$$g\mu H_{\max} \sim \sqrt{3(\Gamma^2 + (\hbar\omega)^2)} [1 + K(1 - \eta)], \quad (19)$$

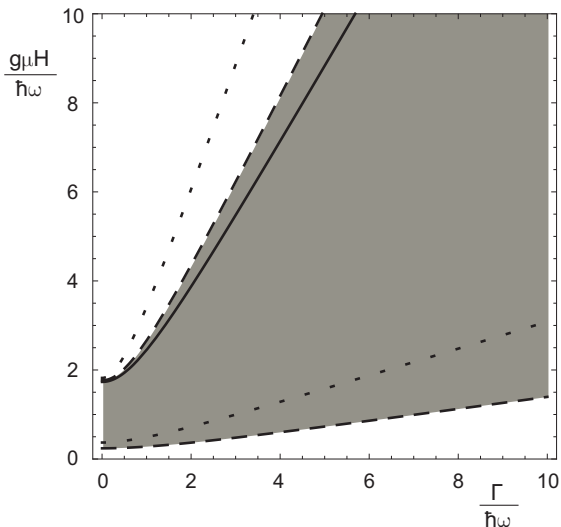


FIG. 1: Upper critical magnetic field (upper set of curves) and lower critical field (lower set of curves) for the shuttle transport regime plotted as a function of the normalized tunneling rate $\Gamma/\hbar\omega$ of majority spin electrons for different values of spin polarization η . The solid curves were plotted for $\eta = 1$ [100% spin polarization, here the lower curve coincides with the x -axis], the dashed curves were plotted for $\eta = 0.8$, and the short-dashed curves for $\eta = 0.3$. The shuttle regime corresponds to the area between the lower and upper critical fields (dark region for the case of $\eta = 0.8$), while outside this area one is in the vibronic regime.

where $K \sim 1$ is a positive constant.

The dependence of the lower critical magnetic field on η is weaker. In the antiadiabatic regime one finds that

$$g\mu H_{\min} \sim \hbar\omega\sqrt{1-\eta}, \quad \Gamma \ll \hbar\omega, \quad (20)$$

and hence H_{\min} rapidly saturates to a constant value of order $\hbar\omega/g\mu$ with decreasing spin polarization (see Fig. 2, short-dashed curve). In the adiabatic regime, $\Gamma \gg \hbar\omega$, the lower critical field decreases linearly with increasing spin polarization, except in the close vicinity of complete spin polarization, where $H_{\min} \propto \sqrt{1-\eta}$ (compare the solid curve in Fig. 2).

The appearance of an upper and a lower critical magnetic field has a simple physical explanation. When μH is the largest energy scale in our problem, $\mu H \gg \Gamma, \hbar\omega$, the fast precession of the electron spin of the dot in a perpendicular external magnetic field nullifies the average spin and the magnetic shuttle instability disappears. To estimate the upper field one may compare the characteristic spin precession frequency, $\mu H_{\max}/\hbar$, with the electron tunneling rate, Γ/\hbar , or the frequency of vibrations ω . That is $\mu H_{\max} \sim \max(\Gamma, \hbar\omega)$. The lower critical field can be readily estimated for a high degree of spin polarization, $1-\eta \ll 1$. In this case we have to compare the average time between spin flips, τ_f , induced by a constant magnetic field H in the presence of an electron tunneling coupling Γ with the characteristic life-time of minority

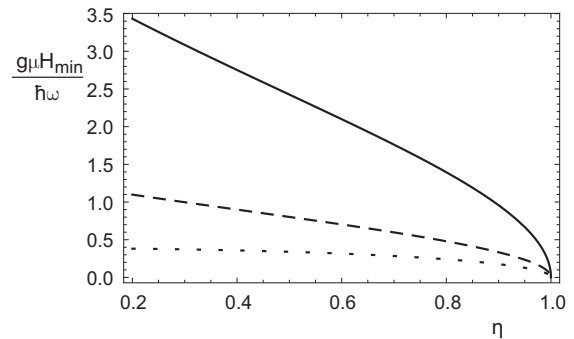


FIG. 2: Plots of the lower critical magnetic field H_{\min} , which defines the border between the vibronic regime ($H < H_{\min}$) and the shuttle transport regime ($H > H_{\min}$; compare Fig. 1) vs. spin polarization η for different values of the normalized tunneling rate $\Gamma/\hbar\omega$ of majority spin electrons (solid curve: $\Gamma/\hbar\omega = 10$; dashed curve: $\Gamma/\hbar\omega = 3$; short-dashed curve: $\Gamma/\hbar\omega = 0.1$).

spin electrons on the dot, $\sim \hbar/\gamma$. The spin-flip rate ν_f in weak magnetic fields H can be estimated by perturbation theory with the result that $\hbar\nu_f \sim (\mu H)^2/\max(\Gamma, \hbar\omega)$. Therefore the lower magnetic field is strongly sensitive to spin polarization,

$$\mu H_{\min} \sim \sqrt{\Gamma\gamma} \max(\Gamma, \hbar\omega) \sim \sqrt{1-\eta} \max(\Gamma, \hbar\omega), \quad (21)$$

and disappears for 100% spin-polarized electrons ($\eta = 1$).

Next we estimate the maximum rate of (exponential) increase, $r_m = -\text{Im}\{\Omega(H_{\text{opt}})\}$, of the QD oscillation amplitude in the shuttle regime. In the adiabatic limit, $\Gamma \gg \hbar\omega$, one finds that $g\mu H_{\text{opt}} \simeq 0.4\Gamma$ and that

$$r_m \simeq C \frac{\omega J}{\Gamma} \left(\frac{x_0}{l}\right)^2, \quad (22)$$

where $C \sim 0.1$ is a small numerical factor. In the case $\Gamma \ll \hbar\omega$, which we are interested in here, the maximum rate is realized when $g\mu H_{\text{opt}} \simeq \hbar\omega$, corresponding to

$$r_m \simeq \frac{\Gamma}{\hbar} \frac{J}{\hbar\omega} \left(\frac{x_0}{l}\right)^2, \quad (23)$$

where we omit a numerical factor of the order of one.

In the presence of dissipation in the mechanical subsystem, which can be described by adding a phenomenological friction term $\gamma_d \dot{x}_c(t)$ to the equation of motion (9) ($\gamma_d = \omega/Q$, where Q is the quality factor), the shuttling regime appears when $r_m > \omega/Q$. Therefore electron shuttling in a C_{60} -based molecular transistor with magnetic electrodes could be realized if the quality factor Q of the mechanical resonator obeys the inequality

$$Q > Q_{\text{opt}} = \frac{(\hbar\omega)^2}{J\Gamma} \left(\frac{l}{x_0}\right)^2. \quad (24)$$

For the experimental setup in Ref. 4, where fullerene vibrations were observed, the factor $(l/x_0)^2 \simeq 10^3$ and

$\Gamma \ll \hbar\omega \sim 5$ meV (one can estimate $\Gamma \sim 0.1 - 0.5$ meV from the maximal current measured in Ref. 4). In the C_{60} -based transistor with magnetic (Ni) leads $J \sim \Gamma \sim 10$ meV (see Ref. 7). From Eq. (24) one can estimate that the required quality factor is $Q \geq 10^3 - 10^4$. However the optimal external magnetic field in this case, $H_{\text{opt}} \simeq 50$ T, is too high. Instead, we therefore estimate Q for magnetic fields in the vicinity of the lower critical magnetic field $H \geq H_{\text{min}}$ where magnetic fields for a very high degree of electron spin polarization ($\sim 99\%$) could be of the order of a few tesla. In this case ($\hbar\omega \gg \Gamma$, $1 - \eta \ll 1$)

$$r(\eta) \simeq \omega \frac{J\Gamma(1-\eta)}{\Gamma^2 + 4(1-\eta)(\hbar\omega)^2} \left(\frac{l}{x_0}\right)^2. \quad (25)$$

Assuming that $\Gamma \simeq \sqrt{1-\eta}\hbar\omega$ we find $Q \sim Q_{\text{opt}}/(1-\eta)$.

4. CONCLUSIONS

In summary we have considered the feasibility of observing magnetically driven single-electron shuttling under realistic conditions corresponding to an already experimentally realized C_{60} -based single-molecule transistor with magnetic leads. The main requirement for magnetic shuttling is the presence of an external magnetic field that induces electron spin flips. We have shown that the optimal magnetic field, defined as the field that maximizes the rate of increase of the shuttling amplitude, is determined by the vibration frequency ω . For fullerene-based single-electron transistors this frequency could be in the THz region [4] with corresponding magnetic fields in the region of several tenths of teslas. For magnetic electrodes with a very high degree of spin polarization one needs less strong (by an order of magnitude) magnetic fields. However, the quality factor of the corresponding mechanical resonator has to be exceptionally high, $Q \geq 10^5$.

Acknowledgements: Financial support from the Leading Foreign Research Institutes Recruitment Pro-

gram (2009-00514) of NRF, Korea, and the Swedish Research Council (VR) is gratefully acknowledged. OI, IK and SK acknowledge financial support from National Academy of Science of Ukraine, Grant No 4/15-N. IK and SK thank the Department of Physics at the University of Gothenburg and the Department of Physics and Astronomy at Seoul National University for their hospitality.

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 - [13] Notice that in Eq. (8) of Ref. 12 (analogous to Eq. (7) of the present paper) there are misprints. The corrections are as follows - minus sign in the h -term and the terms $\Gamma_S^\uparrow(x)$ and $\Gamma_S^\downarrow(x)$ have to be omitted.